ABSTRACT

A plasma processing method includes: (A) performing plasma processing on a substrate introduced into a processing chamber, (B) calculating a thickness of a reaction product deposited on the substrate by (A), (C) setting a time for dry cleaning to remove a reaction product deposited inside the processing chamber by (A) based on the thickness of the reaction product calculated in (B), and (D) performing the dry cleaning for the time set in (C) in a state where the substrate is unloaded from the processing chamber.

Fig. 7